

LIST OF CONTRIBUTIONS TO NATIONAL AND INTERNATIONAL CONGRESSES 2016

1. Rafí, J.M.; Pellegrini, G.; Quirion, D.; Hidalgo, S.; Godignon, P.; Matilla, O.; Juanhuix, J.; Fontserè, A.; Molas, B.; Pothin, D.; Fajardo, P.
10 um-thick Four-quadrant Transmissive Silicon Photodiodes for Beam Position Monitor Application: Electrical Characterization and Gamma Irradiation Effects.
International Workshop on Radiation Imaging Detectors; International
2. Victor Soler; Maria Cabello; Josep Montserrat; José Rebollo; José Millán; Philippe Godignon; Maxime Berthou; Enea Bianda; Andrei Mihaila.
4.5 kV SiC MOSFET with Boron Doped Gate Dielectric
International Symposium on Power Semiconductor Devices and ICs (ISPSD); International;
3. V.Soler; M.Cabello; M.Berthou; J.Montserrat; J.Rebollo; J.Millán; P.Godignon; E.Bianda; A.Mihaila.
4H-SiC MOSFETs de 5 kV con óxido de puerta dopado con Boro.
Seminario Anual de Automática, Electrónica Industrial e Instrumentación (SAAEI); National;
4. Victor Soler; Maria Cabello; Maxime Berthou; Josep Montserrat; Philippe Godignon; José Rebollo; José Millán.
Analysis of Conduction Mode of SiC L-IGBT.
European Materials Research Society (E-MRS); International;
5. V.Soler; M.Berthou; J.Montserrat; P. Godignon; J.Rebollo; J.Millán.
Analysis of conductivity modulation in SiC IGBTs.
European Materials Research Society (E-MRS); International;
6. Fernández-Martínez, P.; Flores, D.; Hidalgo, S.; Quirion, D.; Ullán, M.; Durà, R.
A new Vertical JFET Technology for Harsh Radiation Applications.
International Seminar on Power Semiconductors; International;
7. Fernández-Martínez, P.; Flores, D.; Hidalgo, S.; Quirion, D.; Ullán, M.
A New Vertical JFET Technology for the Powering Scheme of the ATLAS Upgrade Inner Tracker.
IEEE Nuclear Science Symposium and Medical Imaging Conference; International;
8. Rodríguez Rogina, María; Rodríguez Alonso, Alberto; Godignon, Philippe; Soler, Victor; Sebastián Zúñiga, Francisco Javier.
Caracterización de la impedancia de puerta y análisis de las características estáticas y dinámicas de MOSFET de SiC de 3,3 kV.
Seminario Anual de Automática, electrónica industrial e Instrumentación (SAAEI); National;

9. Jordà, X.; Perpiñà, X.; Vellvehí, M.; Fernández, M.; Llorente, S.; Aranda, S.
Characterization of Thermal Interface Materials for IGBT Inverter Applications.
International Workshop on THERMal INvestigations of ICs and Systems; International;
10. P. Fernández-Martínez; M. Ullán; D. Flores; S. Hidalgo; D. Quirion.
Development of a rad-hard switch for the HV power distribution in the ATLAS-Upgrade.
Fifth Common ATLAS CMS Electronics Workshop for LHC Upgrades; International;
11. Garcia-Garcia, A.; Serrano, L.; Ballestar, A.; Rius, G.; Godignon, P.; Ibarra, R.; de Teresa, J.M.
Epitaxial graphene on SiC: a route towards high-performance electronic devices.
Graphene Industry Challenges and opportunities; International;
12. Fernández-Martínez, P.; Flores, D.; Quirion, D.; Ullán, M.; Hidalgo, S.
Fabrication of the first 3D Vertical JFET at the IMB-CNM.
Topical Workshop on Electronics for Particle Physics; International;
13. Carulla, M.; Pellegrini, G.; Hidalgo, S.; Flores, D.
First LGAD fabrication on 50um SOI wafers at CNM for the HGTD.
Workshop on Radiation hard semiconductor devices for very high luminosity colliders; International;
14. Maria Cabello; Victor Soler; Josep Montserrat; Jose Rebollo; Jose Millan; Philippe Godignon.
High mobilities SiC N-MOSFET using nitrated gate oxide with Boron diffusion treatment.
European Materials Research Society (E-MRS); International;
15. M. Cabello; V. Soler; N. Mestres; J. Montserrat; J. Rebollo; J. Millan; P. Godignon.
Impact of channel mobility improvement using Boron diffusion on different Power MOSFETs voltage classes
European Conference on Silicon Carbide & Related Materials (ECSCRM); International;
16. Cabello, M.; Soler, V.; Mestres, N.; Montserrat, J.; Rebollo, J.; Millán, J.; Godignon, P.
Improved 4H-SiC N-MOSFET interface passivation by combining N₂O with Boron diffusion oxidation.
European Conference on Silicon Carbide and Related Materials; International;
17. R. Rodriguez-Rodriguez, M. Pozo, M. Calderon-Domínguez, L. Herrero, D. Serra, M. Vellvehí; X. Perpiñà, N. Casals.
Lack of brain-specific carnitine palmitoyltransferase 1C (CPT1C) impairs leptin- and diet-induced thermogenesis.

**EMBO workshop on Neural control of metabolism and eating behaviour;
International;**

18. Rius, G.; Evangelio, L.; Perez-Murano, F.; Godignon, P.
Long-range periodic spontaneous directed self-assembly of block copolymers upon epitaxial graphene on silicon carbide.
Workshop on Functional Nanomaterials; International;
19. Baselga, M.; Fernández-Martínez, P.; Flores, D.; Hidalgo, S.; Merlos, A.; Pellegrini, G.; Quirion, D.
Measurement of the Time Resolution of Ultra-Fast Silicon Detectors.
**IEEE Nuclear Science Symposium and Medical Imaging Conference;
International;**
20. N. Flaschel; D. Ariza; S. Diez; M. Gerboles; I. Gregor; X. Jorda; R. Mas; A. Mussgiller; D. Quirion; K. Tackmann; M. Ullan.
Micro-channel Cooling For Silicon Detectors.
**IEEE Nuclear Science Symposium and Medical Imaging Conference;
International;**
21. Alfieri, G.; Mihaila, A.; Nipoti, R.; Puzanghera, M.; Sozzi, G.; Godignon, P.; Millán, J.
Point defects investigation of high-energy proton irradiated SiC p+-i-n diodes.
**European Conference on Silicon Carbide and Related Materials;
International;**
22. Banu, V.; Soler, V.; Montserrat, J.; Millán, J.; Godignon, P.
Power cycling analysis method for high-voltage SiC diodes.
European Symposium on the Reliability of Electron Devices, Failure Physics and Analysis; International;
23. Banu, V.; Brosselard, P.; Jordà, X.; Godignon, P.
Power Cycling and Surge Current Tester for SiC Power Devices.
International Semiconductor Conference; International;
24. T. Phulpin; D. Tremouilles; K. Isoird; P. Austin; J. Leon; M. Vellvehi; X. Perpiñà; X. Jorda.
Robustesse de MESFET SiC face aux décharges électrostatiques.
**Proceedings of the Symposium de Genie Electrique (SGE 2016);
International;**
25. Carulla, M.; Fernández-Martínez, P.; Flores, D.; Hidalgo, S.; Merlos, A.; Pellegrini, G.; Quirion, D.
Status of technological development on LGAD and Future plans.
**Workshop on Radiation hard semiconductor devices for very high
luminosity colliders; International;**
26. Carulla, M.; Hidalgo, S.; Pellegrini, G.; Flores, D.

Technological Developments on iLGAD Detectors for Tracking and Timing Applications.

Workshop on Radiation hard semiconductor devices for very high luminosity colliders; International;

27. J. Altet; A. Rubio; F. Reverter; X. Perpiñà; X. Aragonés; X. Jordà; M. Vellvehi; D. Mateo.

Temperature sensors and measurements to test analogue circuits: questions and answers.

IEEE 21st International Mixed-Signal Testing Workshop (IMSTW); International;

28. Carulla, M.; Flores, D.; Hidalgo, S.; Quirion, D.; Pellegrini, G.

The HGTD: A SOI Power Diode for Timing Detection Applications.

International Seminar on Power Semiconductors; International;

29. I. Serrano-Esparza; S. Sangiao; L. Serrano-Ramón; A. Ballestar; A. García; A. Zurutuza; A. Centeno; P. Godignon; J.M. De Teresa.

Weak localization phenomena in graphene.

TALEM meeting; International;